

N-Channel JFET Low-Frequency Low-Noise Amplifier

BSR57

• This device is designed for low–power chopper or switching application sourced from process 51

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|------------------|-------------|------|
| Drain-Gate Voltage | V_{DGO} | 40 | V |
| Gate-Source Voltage | V_{GSO} | -40 | V |
| Forward Gate Current | I_{GF} | 50 | mA |
| Total Power Dissipation Up to T _{amb} = 40°C | P _{tot} | 250 | mW |
| Storage Temperature Range | T _{STG} | -55 to +150 | °C |
| Junction Temperature | TJ | 150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



- 1. Drain
- Source
 Gate
- SOT-23 CASE 318-08 STYLE 10

MARKING DIAGRAM



M5 = Specific Device Code

M = Date Code ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------|-------------------------|-----------------------|
| BSR57 | SOT-23-3/5 (Pb-Free) | 3000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|---------------------------------|---|------|------|------|-------|
| BV _{GSS} | Gate-Source Voltage | $V_{DS} = 0 \text{ V}, I_{C} = 1.0 \mu\text{A}$ | 40 | - | - | V |
| I _{GSS} | Gate Reverse Current | $V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$ | - | - | 1.0 | nA |
| I _{DSS} | Zero-Gate Voltage Drain Current | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}$ | 20 | - | 100 | mA |
| V _{GS} (off) | Gate-Source Cut-off Voltage | $V_{DS} = 15 \text{ V}, I_D = 0.5 \text{ nA}$ | 2.0 | - | 6.0 | V |
| V _{DS} (on) | Drain-Source On Voltage | $V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}$ | - | - | 0.5 | V |
| r _{ds} (on) | Drain-Source On Reverse | $V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$ | - | - | 40 | Ω |
| C _{rss} | Reverse Transfer Capacitance | $V_{DS} = 0 \text{ V}, V_{GS} = 10 \text{ V}$ | - | - | 5.0 | pF |
| t _d | Delay Time | $V_{DD} = 10 \text{ V}, V_{GS}(on) = 0 \text{ V}$ | - | - | 6.0 | ns |
| t _r | Rise Time | $I_D = 10 \text{ mA}, V_{GS}(\text{off}) = 6.0 \text{ V}$ | - | - | 4.0 | |
| t _{off} | Turn-off Time | | - | - | 50 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

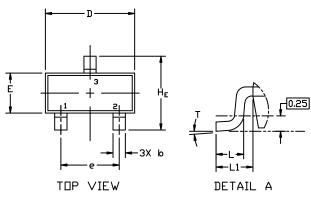


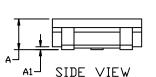


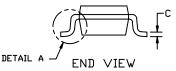
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DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | INCHES | | | |
|-----|-------------|------|--------|-------|-------|-------|
| DIM | MIN. | N□M. | MAX. | MIN. | N□M. | MAX. |
| Α | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| С | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| Ε | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| Т | 0* | | 10° | 0* | | 10° |

GENERIC MARKING DIAGRAM*

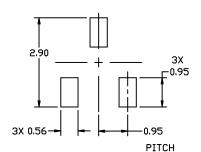


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | ı | |
|---|---|---|--|------------------|------------------|
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: | STYLE 14: |
| PIN 1. ANODE | PIN 1. DRAIN | PIN 1. ANODE | | PIN 1. SOURCE | PIN 1. CATHODE |
| 2. ANODE | 2. SOURCE | 2. CATHODE | | 2. DRAIN | 2. GATE |
| 3. CATHODE | 3. GATE | 3. CATHODE-ANODE | | 3. GATE | 3. ANODE |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: | STYLE 19: | STYLE 20: |
| PIN 1. GATE | PIN 1. ANODE | PIN 1. NO CONNECTION | PIN 1. NO CONNECTION | I PIN 1. CATHODE | PIN 1. CATHODE |
| 2. CATHODE | 2. CATHODE | 2. ANODE | 2. CATHODE | 2. ANODE | 2. ANODE |
| 3. ANODE | 3. CATHODE | 3. CATHODE | 3. ANODE | 3. CATHODE-ANODE | 3. GATE |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: | STYLE 25: | STYLE 26: |
| PIN 1. GATE | PIN 1. RETURN | PIN 1. ANODE | PIN 1. GATE | PIN 1. ANODE | PIN 1. CATHODE |
| 2. SOURCE | 2. OUTPUT | 2. ANODE | 2. DRAIN | 2. CATHODE | 2. ANODE |
| 3. DRAIN | 3. INPUT | 3. CATHODE | 3. SOURCE | 3. GATE | 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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